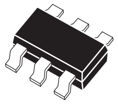
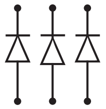
CMKD6263

**SURFACE MOUNT
TRIPLE ISOLATED
HIGH VOLTAGE
SILICON SCHOTTKY DIODES**

ULTRAmini™





SOT-363 CASE

**Central™
Semiconductor Corp.**

FEATURES:

- MEETS GALVANIC ISOLATION REQUIREMENTS OF IEEE 1394
- HIGH VOLTAGE (70V)
- ULTRAmini™ PACKAGE
- REQUIRES LESS BOARD SPACE THAN 3 INDIVIDUAL DIODES
- LOW FORWARD VOLTAGE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD6263 contains three Galvanically isolated, High Voltage Silicon Schottky diodes, epoxy molded in a SOT-363 surface mount package. This ULTRAmini™ device has been designed for fast switching applications requiring a low forward voltage drop.

MARKING CODE: K63

MAXIMUM RATINGS PER DIODE: (T_A=25°C)

	SYMBOL		**UNITS**
Peak Repetitive Reverse Voltage	V_{RRM}	70	V
Continuous Forward Current	I_F	15	mA
Forward Surge Current, tp=1.0 s	I_{FSM}	50	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	500	°C/W

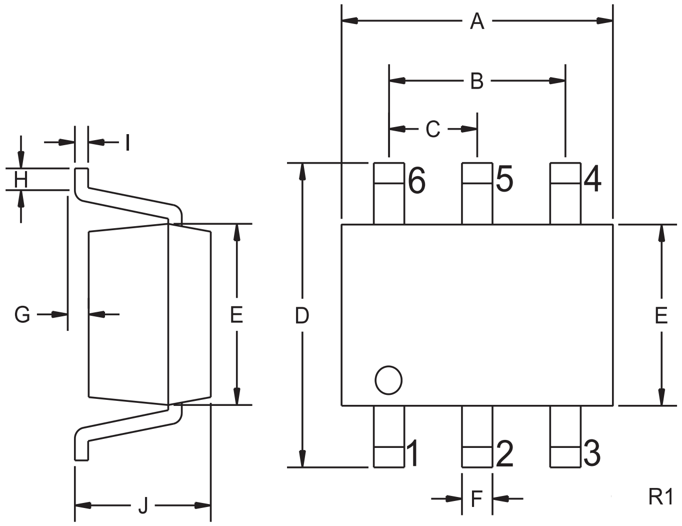
ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C)

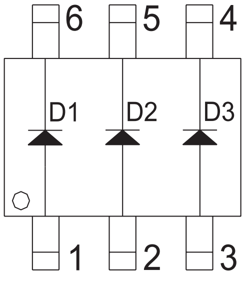
SYMBOL	**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNITS**
BV_R	I_R=10μA	70			V
V_F	I_F=1.0mA		395	410	mV
I_R	V_R=50V		98	200	nA
C_T	V_R=0V, f=1.0MHz			2.0	pF
t_{rr}	I_R=I_F=10mA, I_{rr}=1mA, R_L=100Ω			5.0	ns

CMKD6263

**SURFACE MOUNT
TRIPLE ISOLATED
HIGH VOLTAGE
SILICON SCHOTTKY DIODES**

SOT-363 CASE - MECHANICAL OUTLINE





DIMENSIONS

SYMBOL	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

LEAD CODE:

1) ANODE D1
2) ANODE D2
3) ANODE D3
4) CATHODE D3
5) CATHODE D2
6) CATHODE D1

MARKING CODE: K63

R1 (13-November 2002)